TIPP115, TIPP116, TIPP117 PNP SILICON POWER DARLÍNGTONS

BOURNS®

- 20 W Pulsed Power Dissipation
- 100 V Capability •
- **2 A Continuous Collector Current** •
- **4 A Peak Collector Current**



MDTRAB

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING			VALUE	UNIT
	TIPP115		-60	
Collector-base voltage ($I_E = 0$)	TIPP116	V _{CBO}	-80	V
	TIPP117		-100	
	TIPP115		-60	
Collector-emitter voltage ($I_B = 0$)	TIPP116	V _{CEO}	-80	V
	TIPP117		-100	
Emitter-base voltage		V _{EBO}	-5	V
Continuous collector current		Ι _C	-2	A
Peak collector current (see Note 1)		I _{CM}	-4	A
Continuous base current	Ι _Β	-50	mA	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)	P _{tot}	0.8	W	
Pulsed power dissipation (see Note 3)	P _T	20	W	
Operating junction temperature range	Тj	-55 to +150	°C	
Storage temperature range	T _{stg}	-55 to +150	°C	
Lead temperature 3.2 mm from case for 10 seconds	ΤL	260	°C	

NOTES: 1. This value applies for $t_p \le 0.3$ ms, duty cycle $\le 10\%$.2. Derate linearly to 150°C case temperature at the rate of 0.32 W/°C.3. $V_{CE} = 20$ V, $I_C = 1$ A, $P_W = 10$ ms, duty cycle $\le 2\%$.

PRODUCT INFORMATION

MAY 1989 - REVISED SEPTEMBER 2002 Specifications are subject to change without notice.

TIPP115, TIPP116, TIPP117 PNP SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperature

	PARAMETER		TEST CONDIT	IONS	MIN	ТҮР	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -10 mA (see Note 4)	I _B = 0	TIPP115 TIPP116 TIPP117	-60 -80 -100			V
I _{CEO}	Collector-emitter cut-off current	$V_{CE} = -30 V$ $V_{CE} = -40 V$ $V_{CE} = -50 V$	$V_{BE} = 0$ $V_{BE} = 0$ $V_{BE} = 0$	TIPP115 TIPP116 TIPP117			-2 -2 -2	mA
I _{CBO}	Collector-base cut-off current	$V_{CE} = -60 V$ $V_{CE} = -80 V$ $V_{CE} = -100 V$	$I_{B} = 0$ $I_{B} = 0$ $I_{B} = 0$	TIPP115 TIPP116 TIPP117			-1 -1 -1	mA
I _{EBO}	Emitter cut-off current	V _{EB} = -5 V	$I_{\rm C} = 0$				-2	mA
h _{FE}	Forward current transfer ratio	$V_{CE} = -4 V$ $V_{CE} = -4 V$	I _C = -1 A I _C = -2 A	(see Notes 4 and 5)	1000 500			
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = -8 mA	I _C = -2 A	(see Notes 4 and 5)			-2.5	V
V _{BE}	Base-emitter voltage	V _{CE} = -4 V	I _C = -2 A	(see Notes 4 and 5)			-2.8	V
V _{EC}	Parallel diode forward voltage	I _E = -4 A	I _B = 0	(see Notes 4 and 5)			-3.5	V

NOTES: 4. These parameters must be measured using pulse techniques, $t_p = 300 \ \mu s_{e}$ duty cycle $\leq 2\%$.

5. These parameters must be measured using voltage-sensing contacts separate from the current carrying contacts.



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